

1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. It is used in applications where "high junction operating temperature capability" is required, the maximum rated junction temperature is 150 °C.

2. Features and benefits

- High blocking voltage capability
- Least sensitive gate for highest noise immunity
- High junction operating temperature capability
- High minimum I_{GT} for guaranteed immunity to gate noise
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

3. Applications

- Applications subject to high temperature
- General purpose motor controls
- Lighting controls
- Applications where only positive gate drive is available
- Applications where gate noise or interference may occur

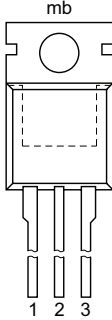
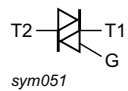
4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--------------------------------------|---|-----|-----|-----|------------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 127\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 8 | A |
| T_j | junction temperature | | - | - | 150 | °C |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(initial)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 65 | A |
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7 | 10 | - | 50 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7 | 10 | - | 50 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7 | 10 | - | 50 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; Fig. 7 | 10 | - | 100 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$; $T_j = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 200 | - | - | V/ μ s |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|---|---|
| 1 | T1 | main terminal 1 |  |  |
| 2 | T2 | main terminal 2 | | |
| 3 | G | gate | | |
| mb | T2 | mounting base; main terminal 2 | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|----------|--|---------|
| | Name | Description | Version |
| BTA137-800G0T | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|--|-----|-----|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 127\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 8 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig 4 ; Fig 5 | - | 65 | A |
| | | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | - | 71 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; sine-wave pulse | - | 21 | A ² s |
| di_T/dt | rate of rise of on-state current | $I_G = 0.1\text{ A}$; T2+ G+ | - | 50 | A/ μ s |
| | | $I_G = 0.1\text{ A}$; T2+ G- | - | 50 | A/ μ s |
| | | $I_G = 0.1\text{ A}$; T2- G- | - | 50 | A/ μ s |
| | | $I_G = 0.2\text{ A}$; T2- G+ | - | 10 | A/ μ s |
| I_{GM} | peak gate current | | - | 2 | A |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T_{stg} | storage temperature | | -40 | 150 | °C |
| T_j | junction temperature | | - | 150 | °C |

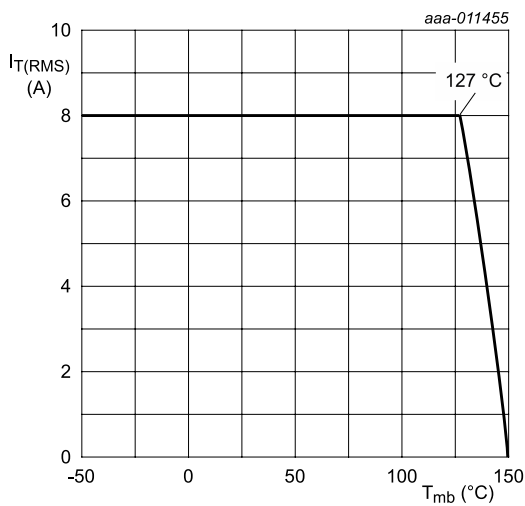
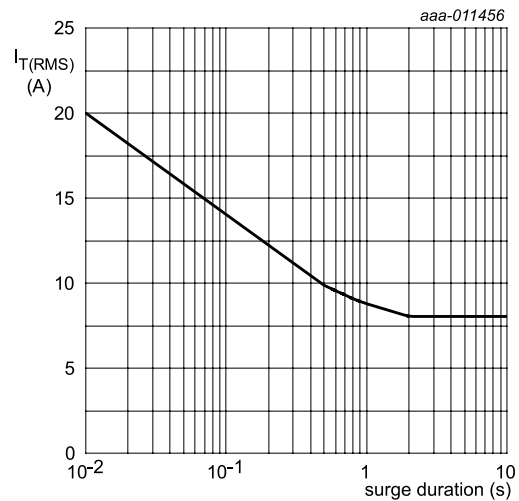


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{mb} \leq 127\text{ °C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

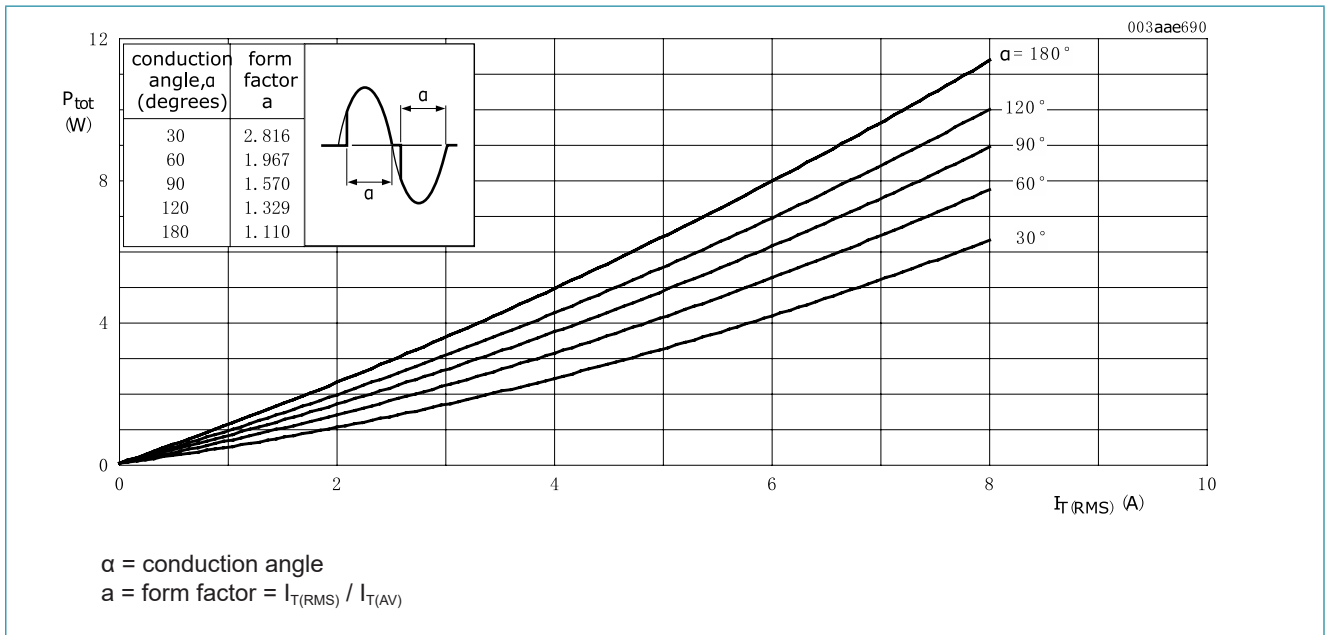


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

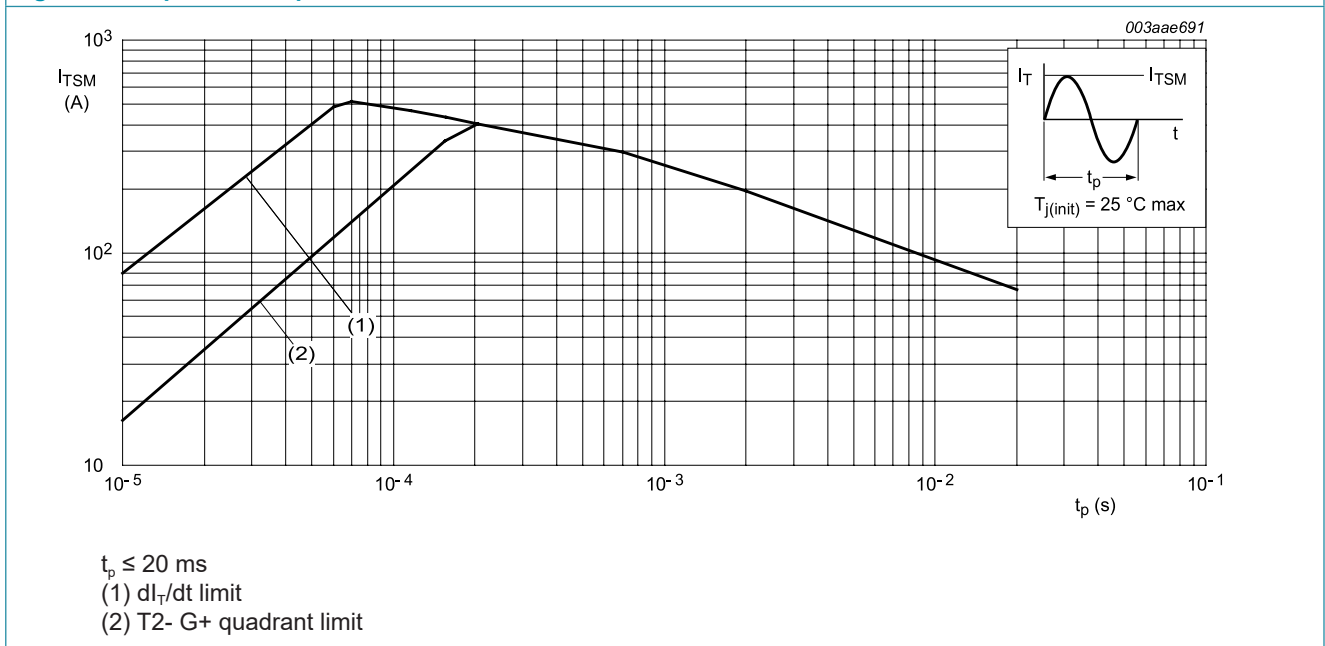
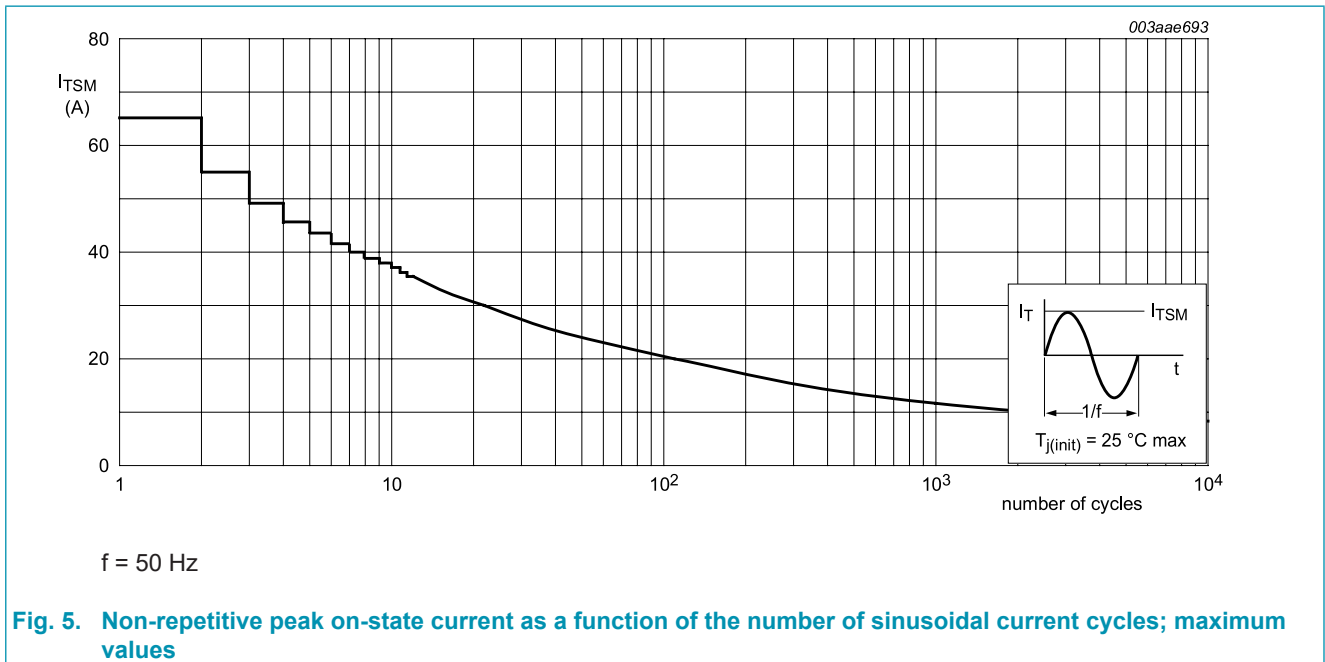


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; Fig. 6 | - | - | 2 | K/W |
| | | half cycle; Fig. 6 | - | - | 2.4 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

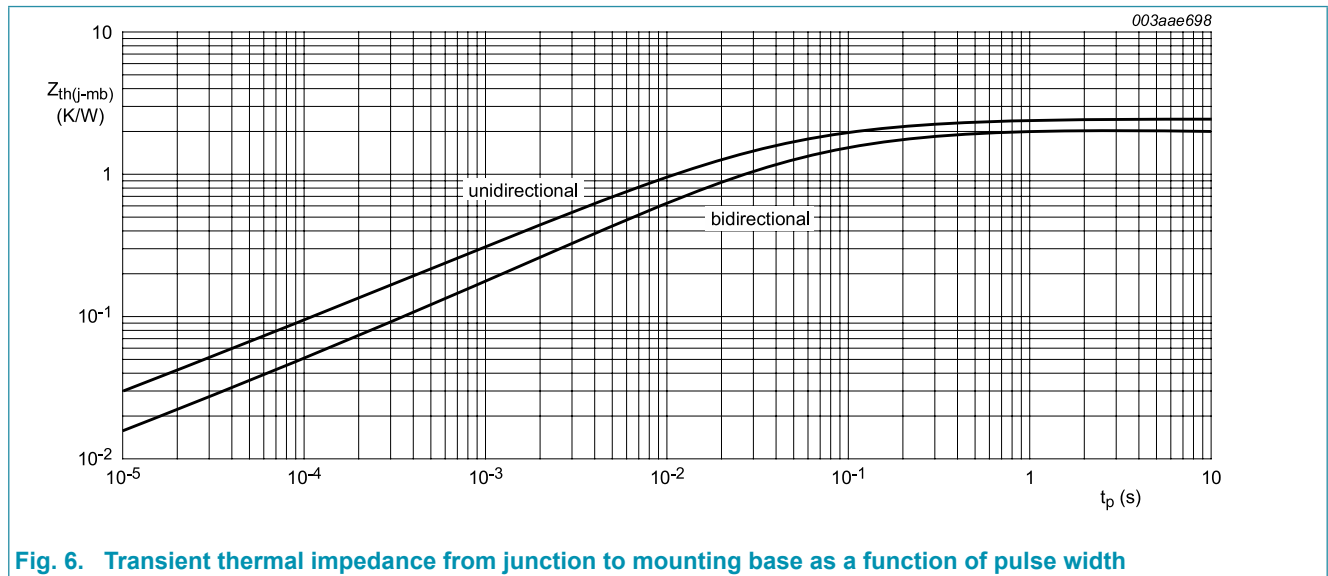
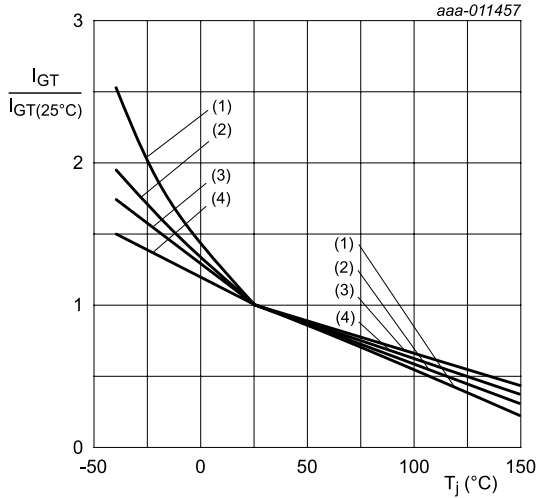


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|------|-----|------|------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | 10 | - | 50 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | 10 | - | 50 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | 10 | - | 50 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | 10 | - | 100 | mA |
| I_L | latching current | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 45 | mA |
| | | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 60 | mA |
| | | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 45 | mA |
| | | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 60 | mA |
| I_H | holding current | $V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9 | - | - | 40 | mA |
| V_T | on-state voltage | $I_T = 10\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10 | - | 1.3 | 1.65 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 11 | - | 0.7 | 1 | V |
| | | $V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 150\text{ }^\circ\text{C};$ Fig. 11 | 0.25 | 0.4 | - | V |
| I_D | off-state current | $V_D = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$ | - | 0.4 | 2 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}; T_j = 150\text{ }^\circ\text{C}; (V_{DM} = 67\%$ of $V_{DRM});$ exponential waveform; gate open circuit | 200 | - | - | V/ μ s |
| dV_{com}/dt | rate of change of commutating voltage | $V_D = 400\text{ V}; T_j = 150\text{ }^\circ\text{C}; dI_{com}/dt = 3.6\text{ A/}$ ms; $I_T = 8\text{ A};$ gate open circuit | 10 | - | - | V/ μ s |
| t_{gt} | gate-controlled turn-on time | $I_{TM} = 12\text{ A}; V_D = 800\text{ V}; I_G = 0.1\text{ A};$ $dI_G/dt = 5\text{ A}/\mu\text{s}$ | - | 2 | - | μ s |



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

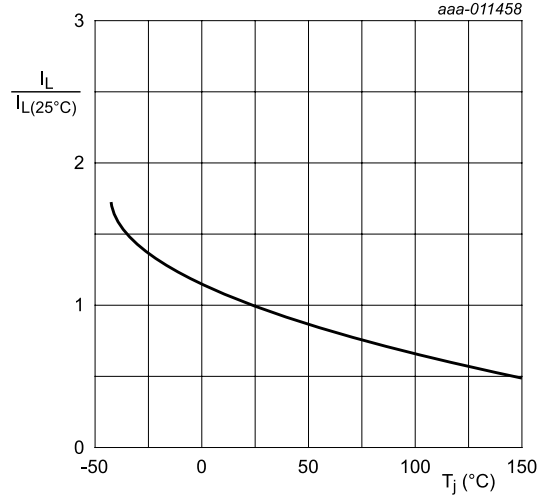


Fig. 8. Normalized latching current as a function of junction temperature

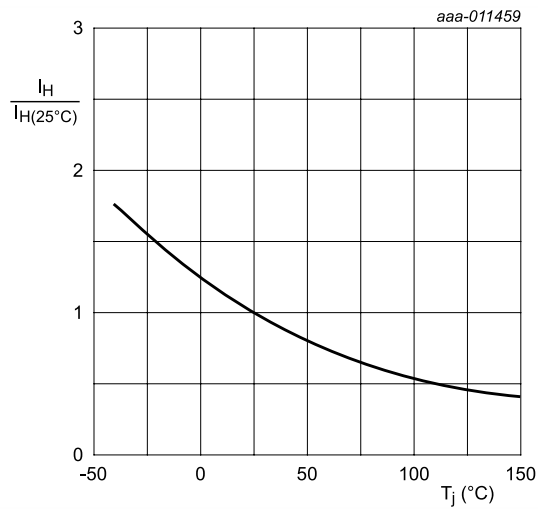
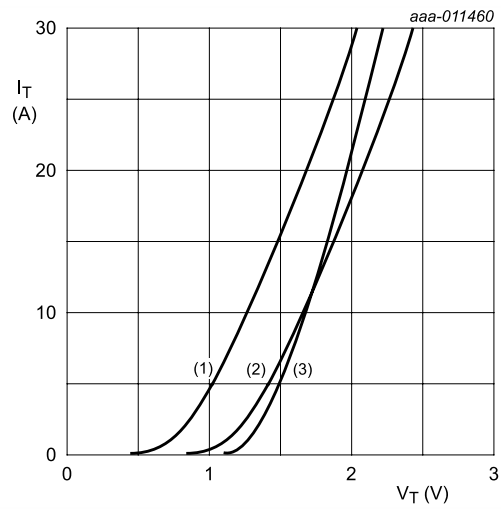


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.264 \text{ V}; R_s = 0.038 \Omega$
- (1) $T_j = 150^{\circ}\text{C}$; typical values
 - (2) $T_j = 150^{\circ}\text{C}$; maximum values
 - (3) $T_j = 25^{\circ}\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

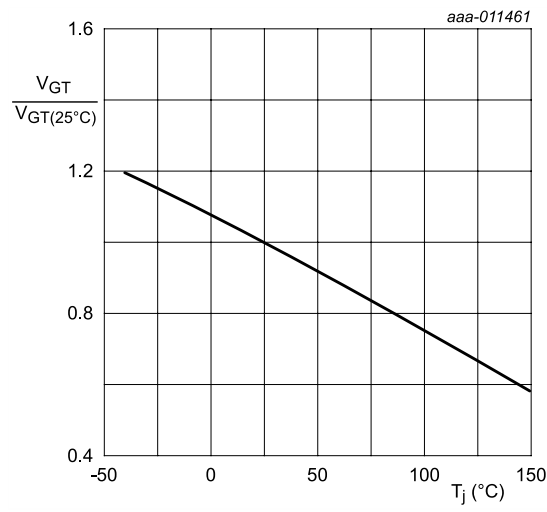


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b | b ₁ (2) | b ₂ (2) | c | D | D ₁ | E | e | L | L ₁ (1) | L ₂ (1) max. | p | q | Q |
|------|------------|----------------|------------|--------------------|--------------------|------------|--------------|----------------|-------------|------|--------------|--------------------|----------------------------|------------|------------|------------|
| mm | 4.7 4.1 | 1.40 1.25 | 0.9 0.6 | 1.6 1.0 | 1.3 1.0 | 0.7 0.4 | 16.0 15.2 | 6.6 5.9 | 10.3 9.7 | 2.54 | 15.0 12.8 | 3.30 2.79 | 3.0 | 3.8 3.5 | 3.0 2.7 | 2.6 2.2 |

Notes

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-----------------|-------|---------------------|----------------------|
| | IEC | JEDEC | JEITA | | |
| SOT78 | | 3-lead TO-220AB | SC-46 | | 08-04-23 08-06-13 |

11. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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